

عنوان مقاله:

A Wide-Band Optimized Distributed Amplifier in 0.13- μm CMOS Technology

محل انتشار:

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خلاصه مقاله:

A 1-25 GHz performance-optimized CMOS distributed amplifier (DA) comprising bandwidth-enhanced cascade cells demonstrated. In this study instead of single resistance, an RL terminating network is used for the gate termination line in order to decrease noise figure (NF). Besides, Deploying the bandwidth extension capacitor, Optimization in cascade gain cells, utilization of bulk-biasing technique, optimization of transistors width and usages of negative-capacitors leads to a flat and high

کلمات کلیدی:

CMOS technology, Distributed Amplifier, Noise Figure, negative-capacitors, Optimization

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